

Dual P-channel Enhancement Mode Power MOSFET

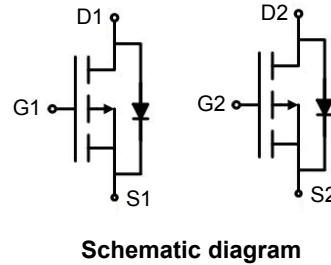
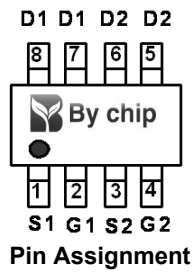
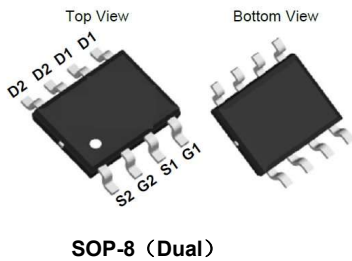
Features

- $V_{DS} = -60V$, $I_D = -5.3 A$
 $R_{DS(ON)} < 54m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)} < 60m\Omega$ @ $V_{GS} = -4.5V$

General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!
100% ΔV_{ds} TESTED!



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ C$)	$T_C = 25^\circ C$	- 5.3 ^e	A
	$T_C = 70^\circ C$	- 5.0 ^e	
	$T_A = 25^\circ C$	- 5.3 ^{a, b}	
	$T_A = 70^\circ C$	- 5.0 ^{a, b}	
Pulsed Drain Current	I_{DM}	- 32 ^e	
Continuous Source-Drain Diode Current	$T_C = 25^\circ C$	- 4.1	
	$T_A = 25^\circ C$	- 2.0 ^{a, b}	
Avalanche Current	I_{AS}	- 20	
Single-Pulse Avalanche Energy	E_{AS}	20	mJ
Maximum Power Dissipation	$T_C = 25^\circ C$	4.0	W
	$T_C = 70^\circ C$	2.5	
	$T_A = 25^\circ C$	2.0 ^{a, b}	
	$T_A = 70^\circ C$	1.4 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	38	50	$^\circ C/W$
Maximum Junction-to-Foot	R_{thJF}	20	25	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 10 s$.
- Maximum under Steady State conditions is $85^\circ C/W$.
- Based on $T_C = 25^\circ C$.
- Limited by package.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	- 60			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 31		$\text{mV}/^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			4.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq -10\text{ V}$, $V_{GS} = -10\text{ V}$	- 30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -5\text{ A}$		0.054		Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -4.5\text{ A}$		0.060		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}$, $I_D = -5\text{ A}$		23		S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1345		pF
Output Capacitance	C_{oss}			210		
Reverse Transfer Capacitance	C_{rss}			180		
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -5\text{ A}$		32	50	nC
		$V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -5\text{ A}$		15	25	
Q_{gs}			4			
Q_{gd}			7.5			
Gate Resistance	R_g	$f = 1\text{ MHz}$		5.8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D \equiv -1\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$		10	15	ns
Rise Time	t_r			8	15	
Turn-Off DelayTime	$t_{d(off)}$			45	70	
Fall Time	t_f			12	25	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}$, $R_L = 15\text{ }\Omega$ $I_D \equiv -1\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$		42	70	
Rise Time	t_r			35	60	
Turn-Off DelayTime	$t_{d(off)}$			40	70	
Fall Time	t_f			16	30	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			- 4.1	A
Pulse Diode Forward Current	I_{SM}				- 32	
Body Diode Voltage	V_{SD}	$I_S = -2\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.75	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$		34	60	ns
Body Diode Reverse Recovery Charge	Q_{rr}			22	40	nC
Reverse Recovery Fall Time	t_a			11		ns
Reverse Recovery Rise Time	t_b			23		

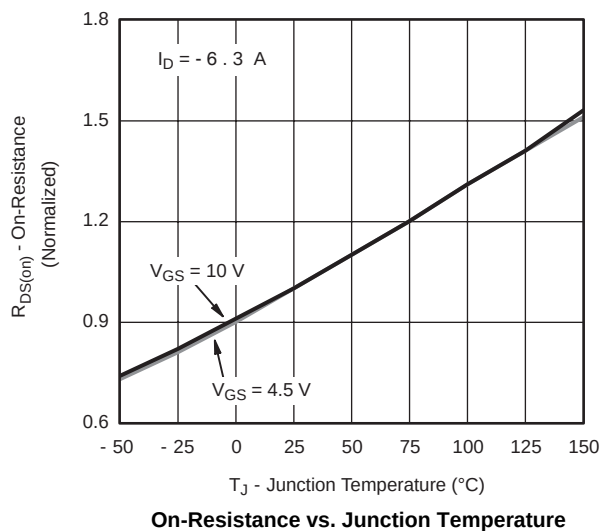
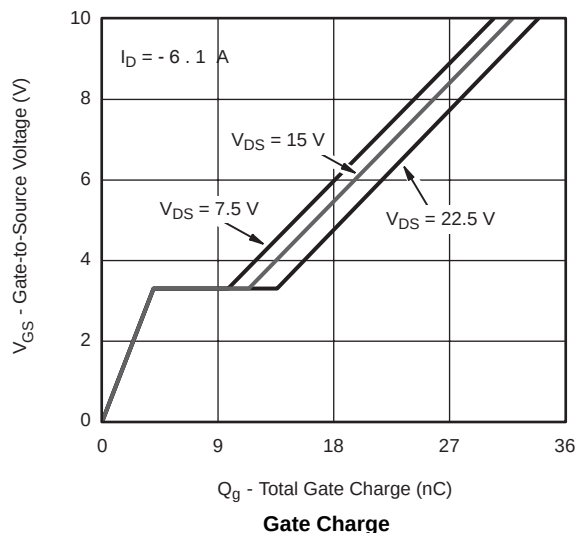
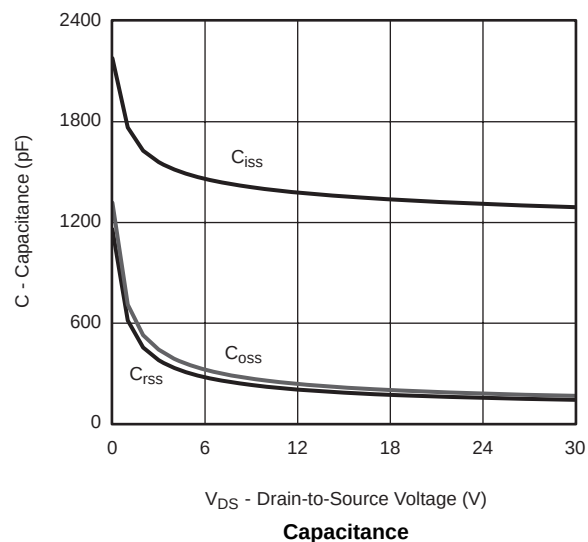
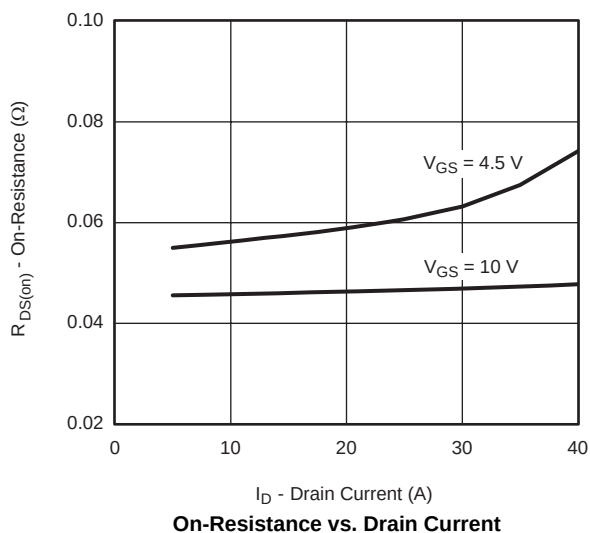
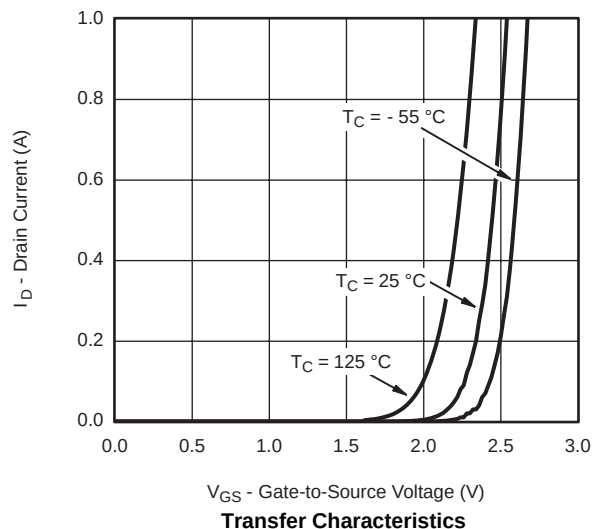
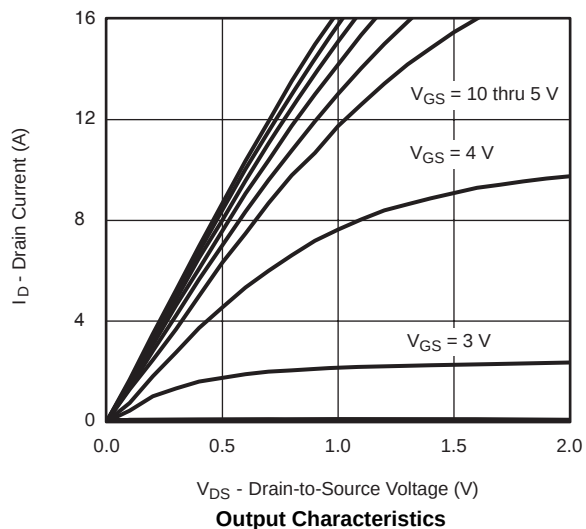
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

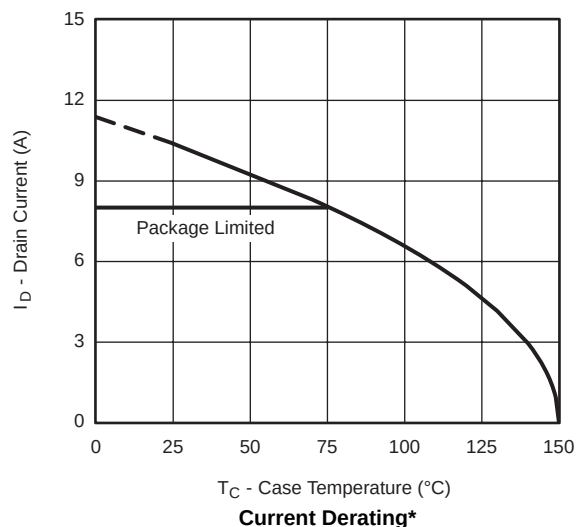
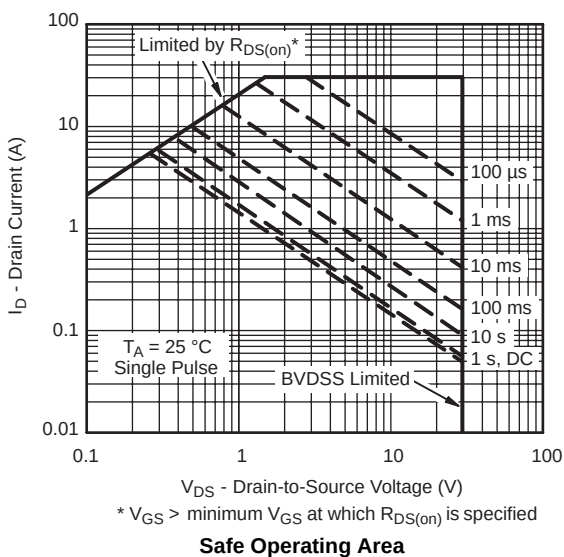
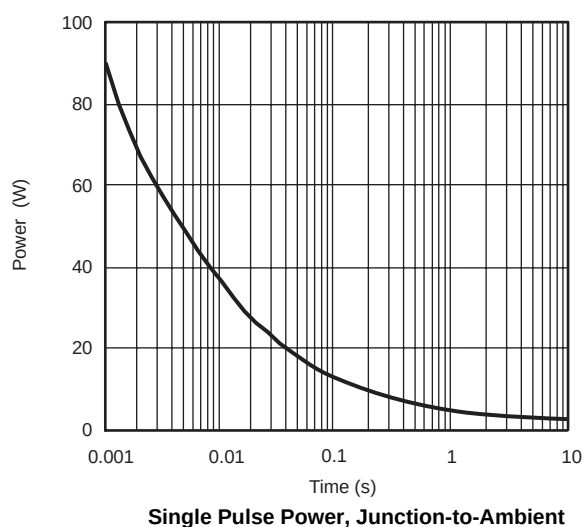
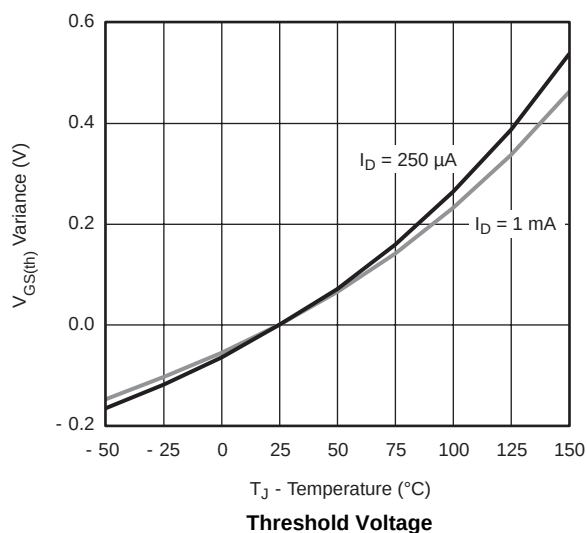
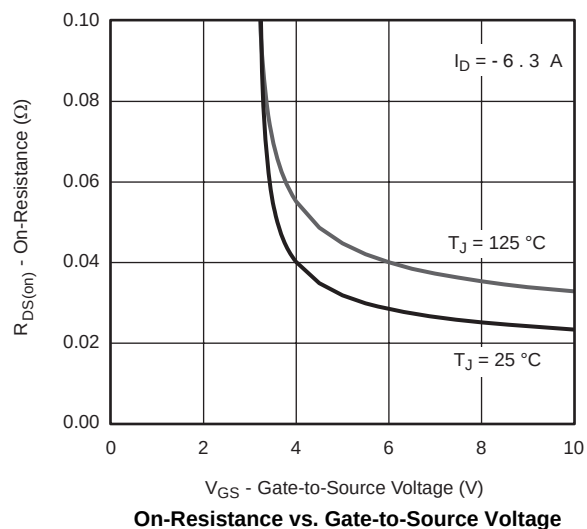
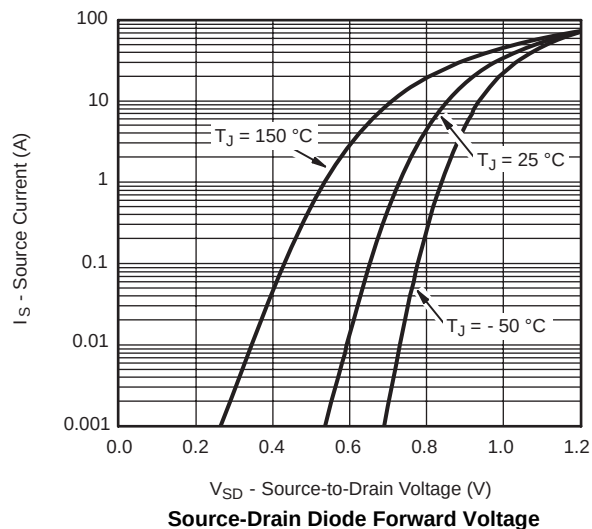
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

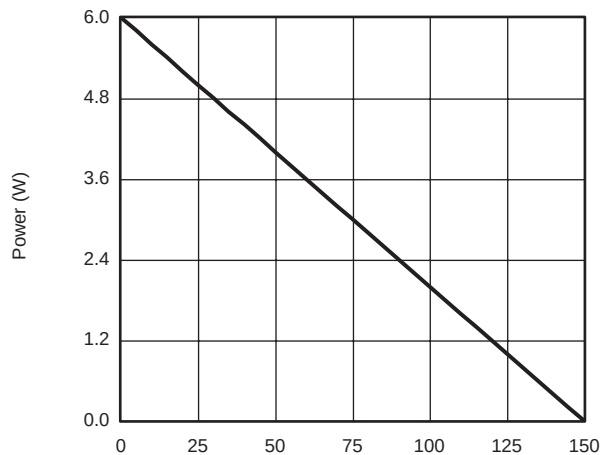
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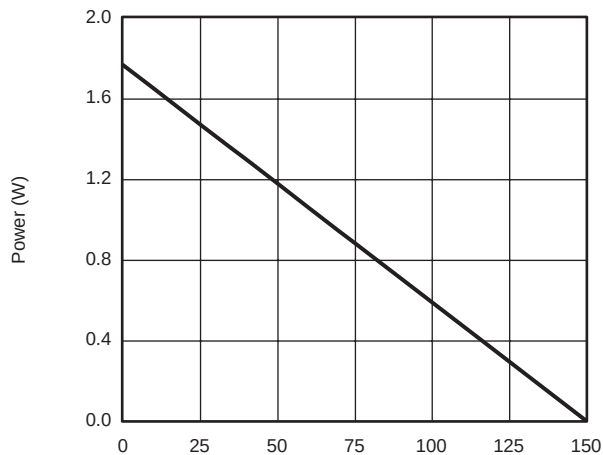


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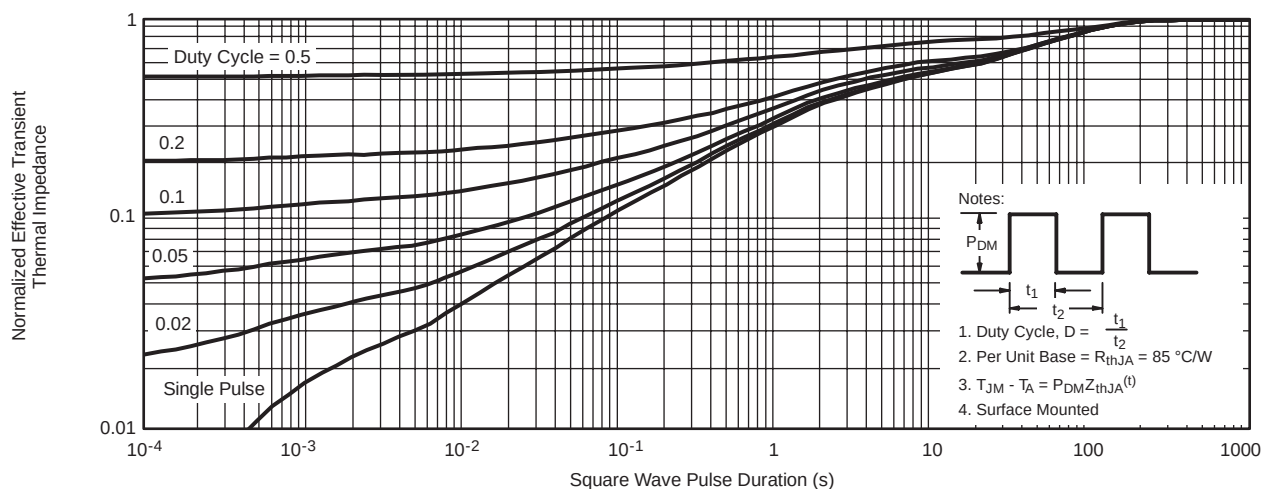
T_C - Case Temperature (°C)

Power, Junction-to-Foot

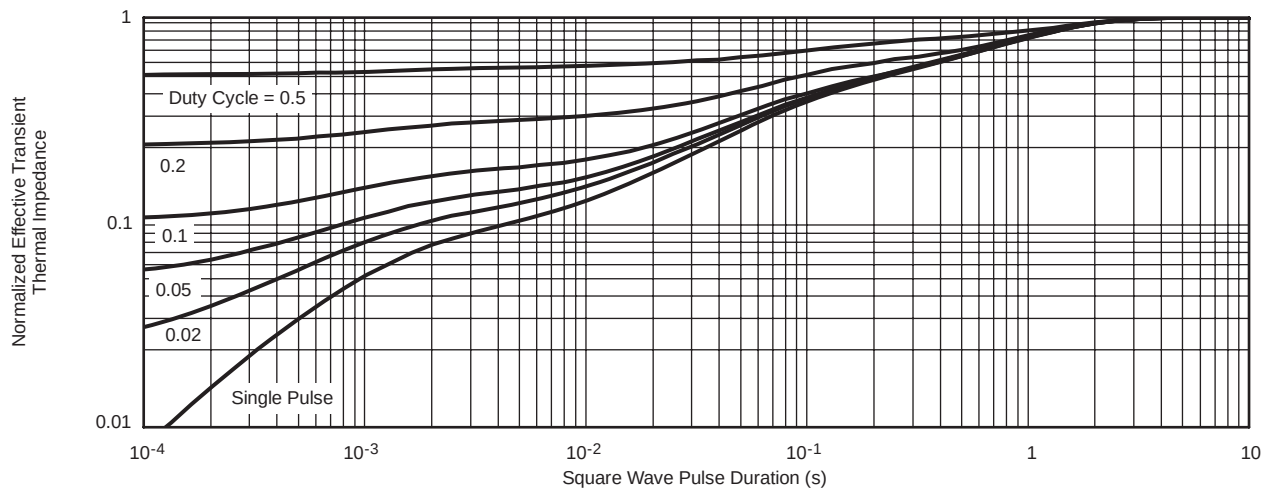


T_A - Ambient Temperature (°C)

Power Derating, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot